

PNP 500 mA, 50 V resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

Rev. 3 — 23 September 2010

Product data sheet

1. Product profile

1.1 General description

500 mA PNP Resistor-Equipped Transistor (RET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTD113ZT.

1.2 Features and benefits

- 500 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

1.4 Quick reference data

Table 1. Quick reference data

Symbol Conditions Unit Parameter Min Тур Max VCEO collector-emitter voltage open base ---50 V I_{O} output current --500 mΑ -R1 0.7 1.0 bias resistor 1 (input) 1.3 kΩ R2/R1 bias resistor ratio 9 10 11

- Reduces pick and place costs
- ±10 % resistor ratio tolerance
- AEC-Q101 qualified
- Cost-saving alternative for BC807 series in digital applications
- Switching loads



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2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline Graphic symbol	
1	input (base)		
2	GND (emitter)	3	- 3
3	output (collector)	1 2 006aaa144 sym003	- 2

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PDTB113ZT	-	plastic surface-mounted package; 3 leads	SOT23		

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
PDTB113ZT	*7W

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
VI	input voltage				
	positive		-	+5	V
	negative		-	-10	V
lo	output current		-	-500	mA

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Limiting values ... continued Table 5.

In accordance with the Absolute Maximum Rating System (IEC 60134).

			,		
Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

Thermal characteristics 6.

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Characteristics 7.

$T_{amb} = 25$ °C unless otherwise specified. Symbol Parameter Conditions Unit Min Тур Max collector-base $V_{CB} = -40 \text{ V}; I_E = 0 \text{ A}$ _ -100 nA I_{CBO} cut-off current $V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$ -100 -nA $V_{CE} = -50 \text{ V}; I_B = 0 \text{ A}$ **I**CEO collector-emitter -_ -0.5 μΑ cut-off current $V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$ emitter-base -0.8 mΑ I_{EBO} -cut-off current DC current gain $V_{CE} = -5 V;$ 70 h_{FE} -- $I_{\rm C} = -50 \, {\rm mA}$ collector-emitter $I_{C} = -50 \text{ mA};$ V V_{CEsat} -0.3-saturation voltage $I_B = -2.5 \text{ mA}$ off-state input voltage $V_{CE} = -5 V;$ V_{I(off)} -0.3 -0.6 -1.0٧ $I_{\rm C} = -100 \ \mu A$ V_{I(on)} $V_{CE} = -0.3 V;$ -0.4 -0.8 -1.4V on-state input voltage $I_C = -20 \text{ mA}$ 1.3 R1 bias resistor 1 (input) 0.7 1.0 kΩ R2/R1 bias resistor ratio 9 10 11 collector capacitance pF C_{c} $V_{CB} = -10 V;$ 11 - $I_{E}=i_{e}=0\;A;$ f = 100 MHz

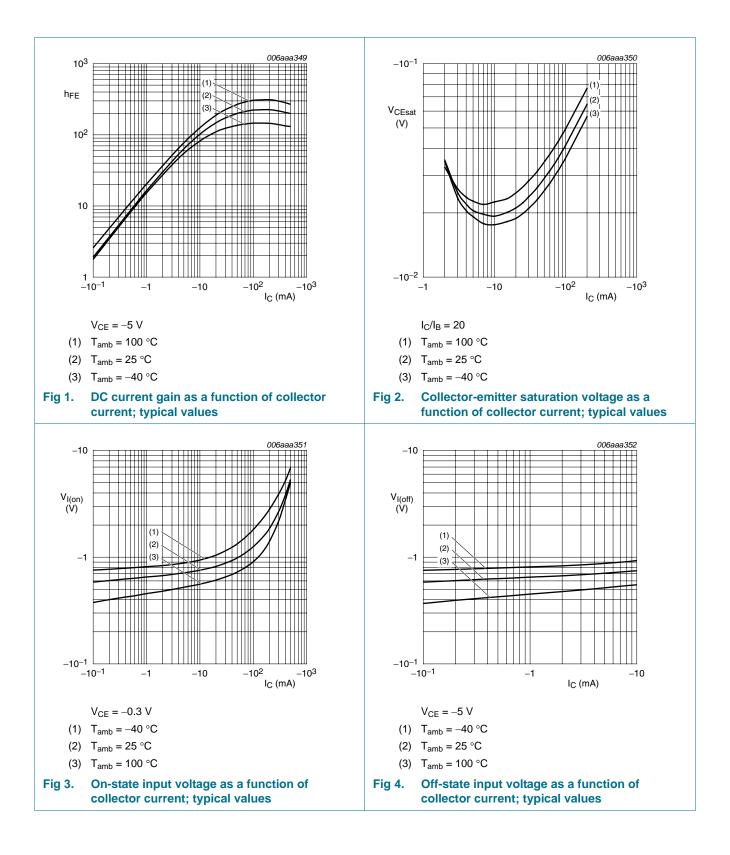
Table 7. **Characteristics**

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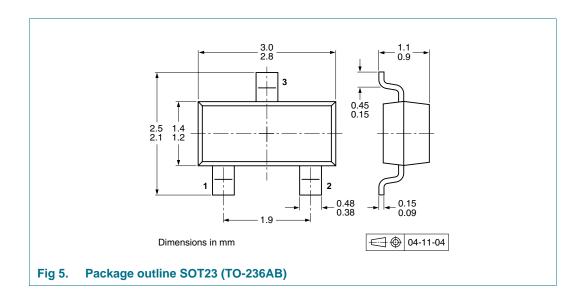
PNP 500 mA resistor-equipped transistor; $R1 = 1 k\Omega$, $R2 = 10 k\Omega$

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

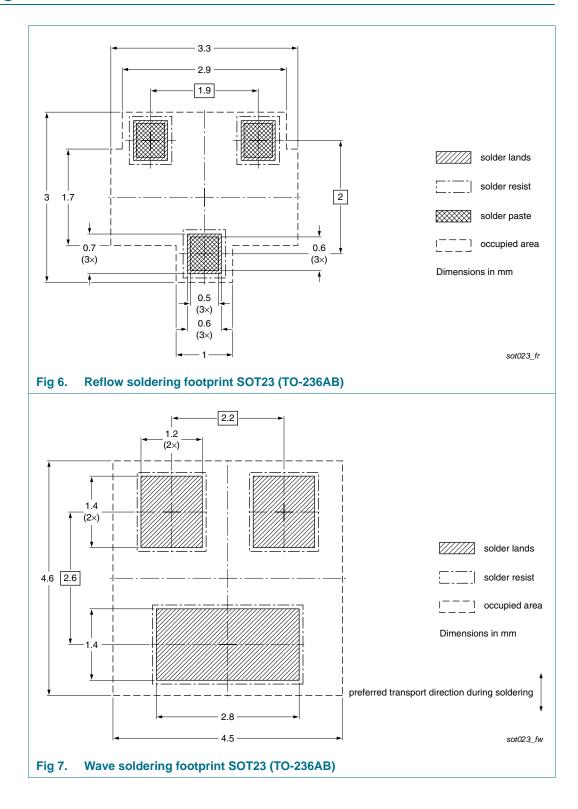
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu	antity
			3000	10000
PDTB113ZT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 14.

PNP 500 mA resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

11. Soldering



12. Revision history

Table 9. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTB113ZT v.3	20100923	Product data sheet	-	PDTB113Z_SER_2
Modifications:	 Type number 	ers PDTB113ZK and PDTB	113ZS deleted.	
	 Table 7 "Characteristic Table 7" 	aracteristics": unit for V _{CEsat}	changed from mV to V	Ι.
	 Section 8 "T 	est information": added.		
	Section 11 "	Soldering": added.		
	 Section 13 " 	Legal information": updated	1.	
PDTB113Z_SER_2	20091116	Product data sheet	-	PDTB113Z_SER_1
PDTB113Z_SER_1	20050427	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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